



Is Now Part of



**ON Semiconductor®**

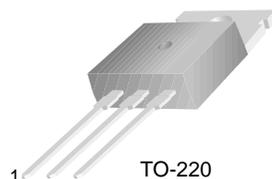
To learn more about ON Semiconductor, please visit our website at  
[www.onsemi.com](http://www.onsemi.com)

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## BDW93/A/B/C

### Hammer Drivers, Audio Amplifiers Applications

- Power Darlington TR
- Complement to BDW94, BDW94A, BDW94B and BDW94C respectively



TO-220  
1.Base 2.Collector 3.Emitter

### NPN Epitaxial Silicon Transistor

#### Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage		
	: BDW93	45	V
	: BDW93A	60	V
	: BDW93B	80	V
	: BDW93C	100	V
$V_{CEO}$	Collector-Emitter Voltage		
	: BDW93	45	V
	: BDW93A	60	V
	: BDW93B	80	V
	: BDW93C	100	V
$I_C$	Collector Current (DC)	12	A
$I_{CP}$	*Collector Current (Pulse)	15	A
$I_B$	Base Current	0.2	A
$P_C$	Collector Dissipation ( $T_C=25^\circ\text{C}$ )	80	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature	- 65 ~ 150	$^\circ\text{C}$

#### Thermal Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
$R_{\theta jc}$	Thermal Resistance	1.5	$^\circ\text{C/W}$
	Junction to Case		

**Electrical Characteristics**  $T_C=25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
$BV_{CEO(sus)}$	* Collector-Emitter Sustaining Voltage : BDW93 : BDW93A : BDW93B : BDW93C	$I_C = 100\text{mA}, I_B = 0$	45 60 80 100			V V V V
$I_{CBO}$	Collector Cut-off Current : BDW93 : BDW93A : BDW93B : BDW93C	$V_{CB} = 45\text{V}, I_E = 0$ $V_{CB} = 60\text{V}, I_E = 0$ $V_{CB} = 80\text{V}, I_E = 0$ $V_{CB} = 100\text{V}, I_E = 0$			100 100 100 100	$\mu\text{A}$ $\mu\text{A}$ $\mu\text{A}$ $\mu\text{A}$
$I_{CEO}$	Collector Cut-off Current : BDW93 : BDW93A : BDW93B : BDW93C	$V_{CE} = 45\text{V}, I_B = 0$ $V_{CE} = 60\text{V}, I_B = 0$ $V_{CE} = 80\text{V}, I_B = 0$ $V_{CE} = 100\text{V}, I_B = 0$			1 1 1 1	mA mA mA mA
$I_{EBO}$	Emitter Cut-off Current	$V_{EB} = 5\text{V}, I_C = 0$			2	mA
$h_{FE}$	* DC Current Gain	$V_{CE} = 3\text{V}, I_C = 3\text{A}$ $V_{CE} = 3\text{V}, I_C = 5\text{A}$ $V_{CE} = 3\text{V}, I_C = 10\text{A}$	1000 750 100		20000	
$V_{CE(sat)}$	* Collector-Emitter Saturation Voltage	$I_C = 5\text{A}, I_B = 20\text{mA}$ $I_C = 10\text{A}, I_B = 100\text{mA}$			2 3	V V
$V_{BE(sat)}$	* Base-Emitter Saturation Voltage	$I_C = 5\text{A}, I_B = 20\text{mA}$ $I_C = 10\text{A}, I_B = 100\text{mA}$			2.5 4	V V
$V_F$	* Parallel Diode Forward Voltage	$I_F = 5\text{A}$ $I_F = 10\text{A}$		1.3 1.8	2 4	V V

\* Pulse Test: PW=300 $\mu\text{s}$ , duty Cycle =1.5% Pulsed

## Typical characteristics

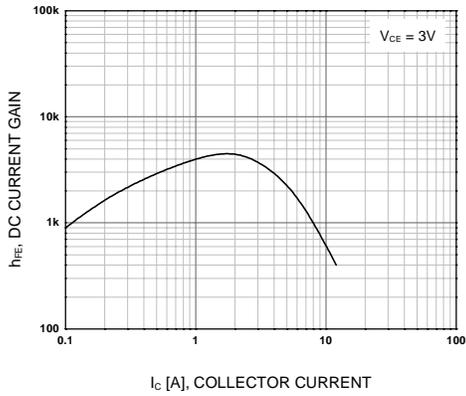


Figure 1. DC Current Gain

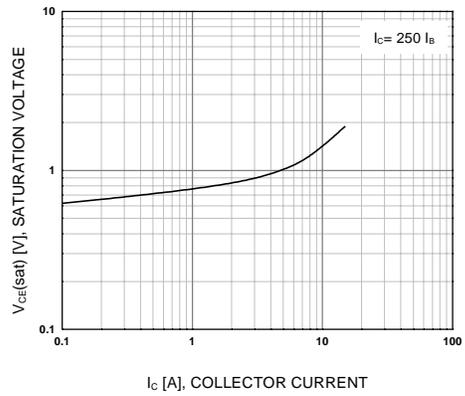


Figure 2. Collector-Emitter Saturation Voltage

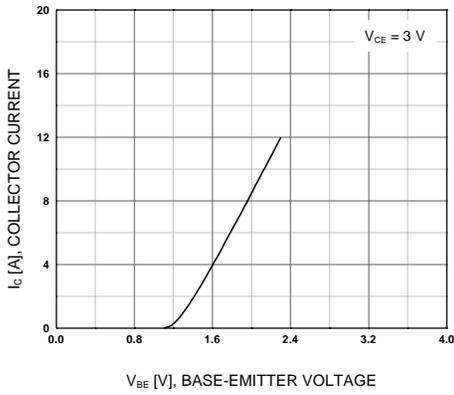


Figure 3. Base-Emitter On Voltage

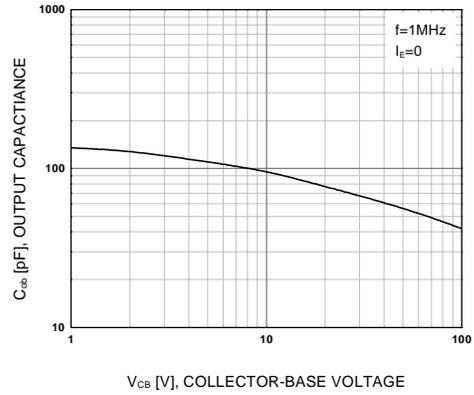


Figure 4. Collector Output Capacitance

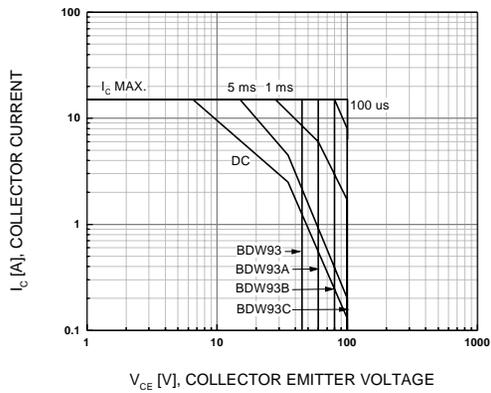


Figure 5. Safe Operating Area

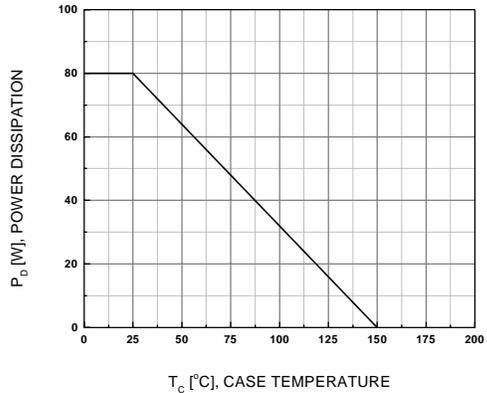
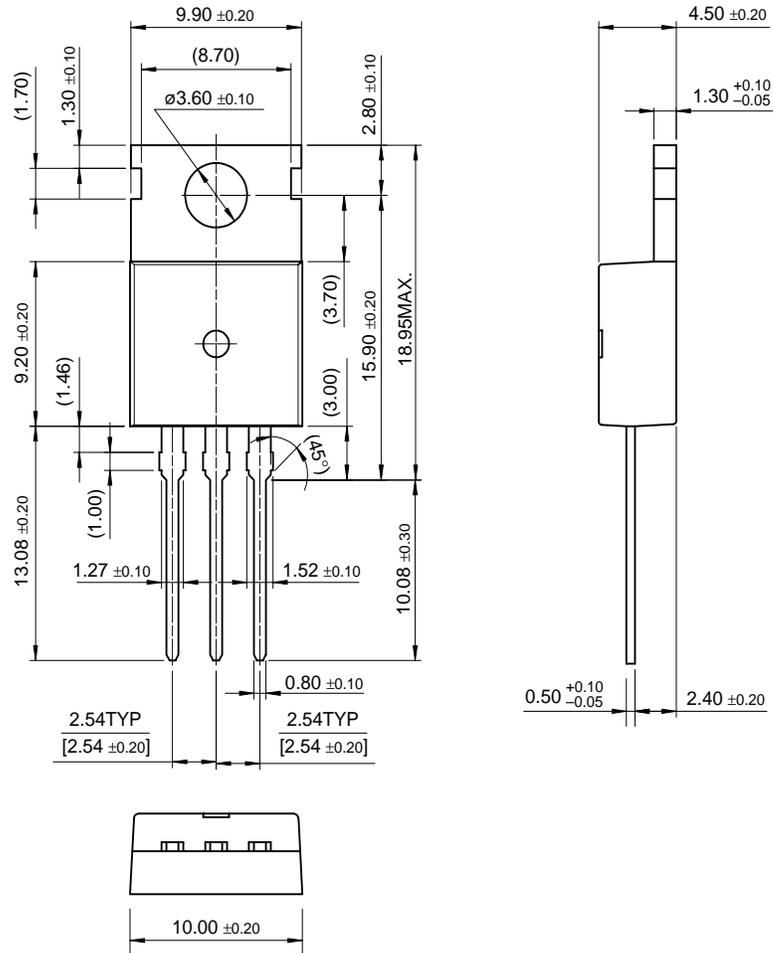


Figure 6. Power Derating

# Package Dimensions

BDW93/A/B/C

## TO-220



Dimensions in Millimeters